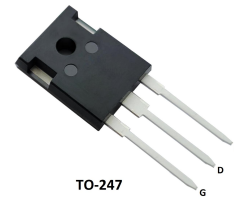


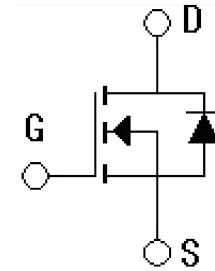
## Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% avalanche tested
- Improved dv/dt capability



## Applications

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)



## Absolute Ratings (Tc=25°C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	650	V
Drain Current-continuous	I <sub>D</sub> T=25°C T=100°C	38	A
		24	A
Drain Current-pulse (note 1)	I <sub>DM</sub>	152	A
Gate-Source Voltage	V <sub>GSS</sub>	±30	V
Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	841	mJ
Avalanche Current (note 1)	I <sub>AR</sub>	7	A
Repetitive Avalanche Current (note 1)	E <sub>AR</sub>	3.9	mJ
Peak Diode Recovery dv/dt (note 3)	dv/dt	50	V/ns
Power Dissipation	PD TC=25°C Derate above 25°C	322	W
		2.58	W/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+175	°C

**Electrical Characteristics**( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Drain-Source Voltage	$BV_{DSS}$	$I_D=500\mu A, V_{GS}=0V$	650	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V, T_C=25^{\circ}C$	-	-	3	$\mu A$
		$V_{DS}=650V, T_C=25^{\circ}C$	-	-	100	$\mu A$
Gate body leakage current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 30V$	-	-	$\pm 100$	nA
<b>On-Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3	3.5	4.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{DS}=10V, I_D=19A$	-	89	109	m $\Omega$
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V, f=1.0MHz$	-	2800	3200	pF
Output capacitance	$C_{oss}$		-	97	-	pF
Reverse transfer capacitance	$C_{rss}$		-	1.5	-	pF

**Electrical Characteristics**( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
<b>Switching-Characteristics</b>						
Turn-On delay time	$t_{d(on)}$	$V_{DD}=100V, I_D=9.0A, R_G=25\Omega, V_{GS}=10V$ (note 4,5)	-	16	-	ns
Turn-On rise time	$t_r$		-	13	-	ns
Turn-Off delay time	$t_{d(off)}$		-	71	-	ns
Turn-Off rise time	$t_f$		-	13	-	ns
Total Gate Charge	$Q_g$	$V_{DS}=480V, I_D=38A, V_{GS}=10V$ (note 4,5)	-	45	55	nC
Gate-Source charge	$Q_{gs}$		-	15	-	nC
Gate-Drain charge	$Q_{gd}$		-	11.5	-	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						

Source-Drain Current (Body Diode)	$I_{SD}$	$T_C=25^{\circ}C$	-		38	A
Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=9.0A$ $di_F/dt=100A/\mu s$ (note 4)		180		ns
Reverse recovery charge	$Q_{rr}$			18		$\mu C$

### Thermal Characteristic

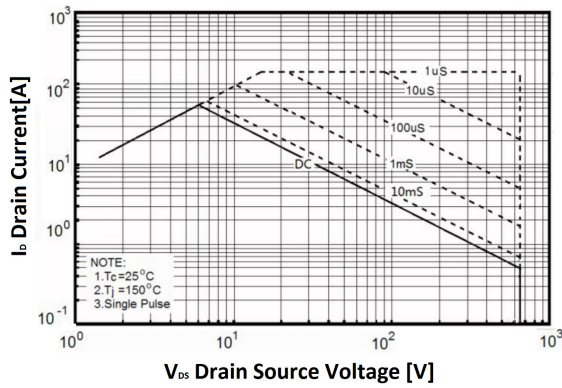
Parameter	Symbol	Value	Unit
Thermal Resistance, junction to Case	$R_{th(j-C)}$	0.39	$^{\circ}C/W$
Thermal Resistance, junction to Ambient	$R_{th(j-A)}$	62	$^{\circ}C/W$

Notes:

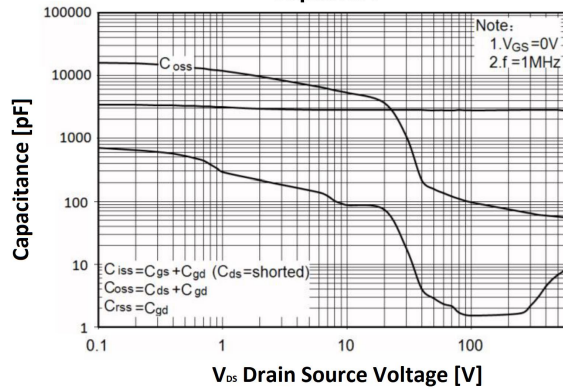
- 1.Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $T_j=25^{\circ}C, V_{DD}=50V, V_G=10V, R =25\Omega$

## Electrical Characteristics

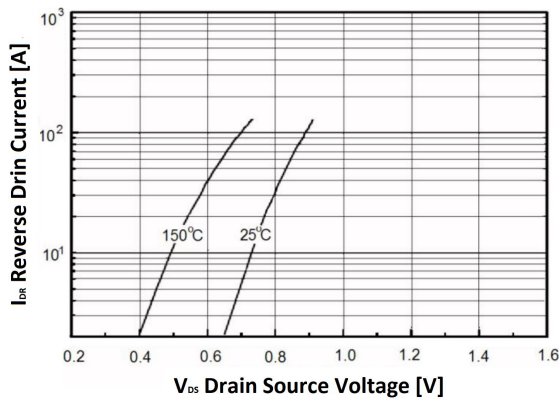
Safe operating area



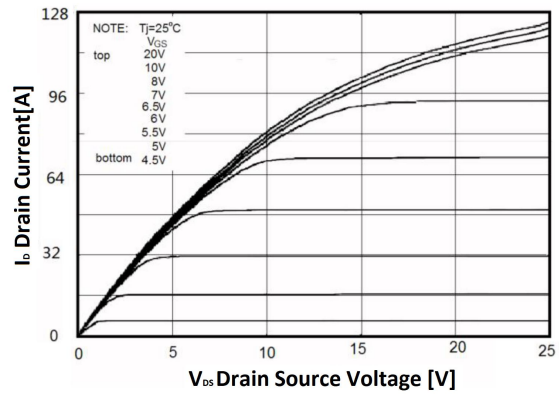
Capacitance



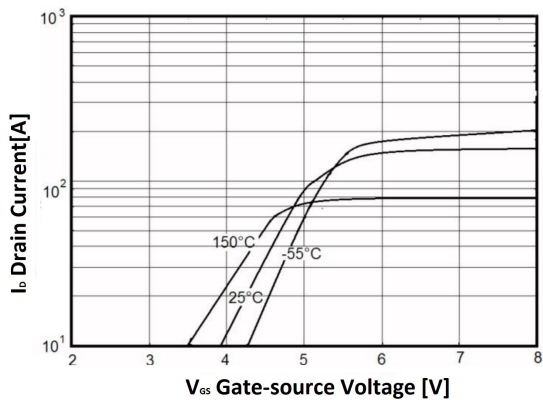
Source-Drain Diode Forward Voltage



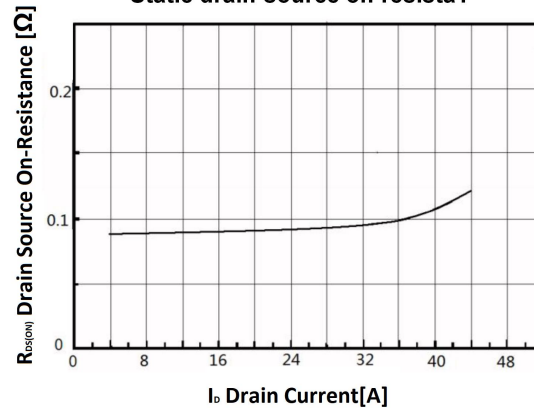
Output characteristics



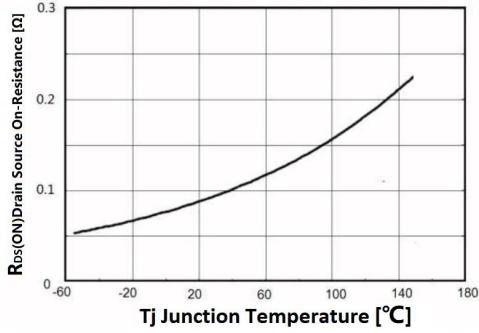
Transfer characteristics



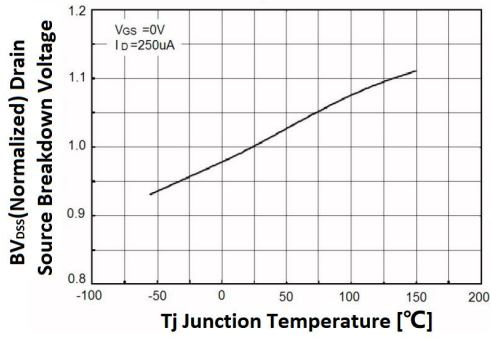
Static drain-source on resistance



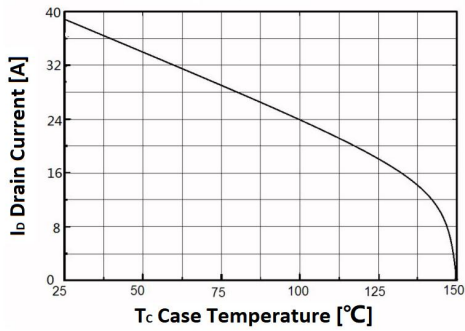
**$R_{DS(ON)}$  vs Junction Temperature**



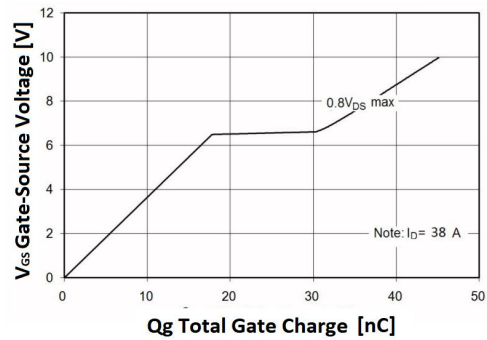
**$BV_{DSS}$  vs Junction Temperature**



**Maximum  $I_D$  vs Junction Temperature**

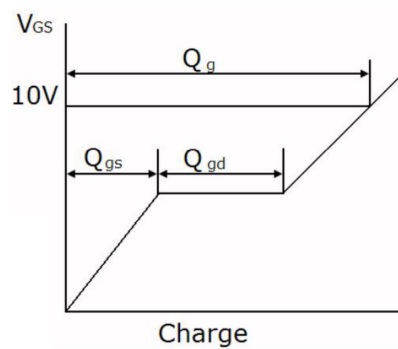
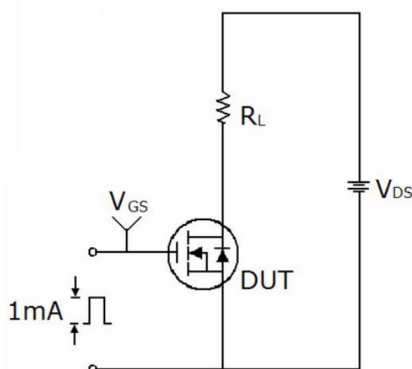


**Gate charge waveforms**

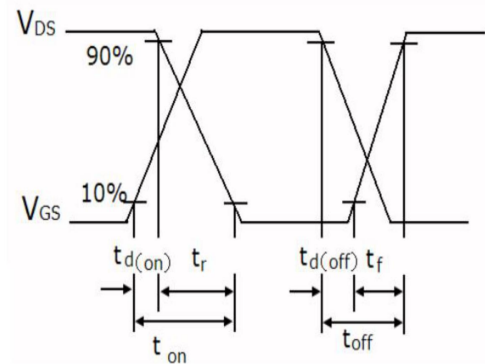
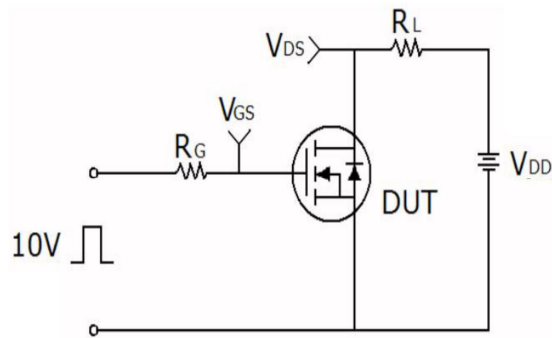


## Test Circuit

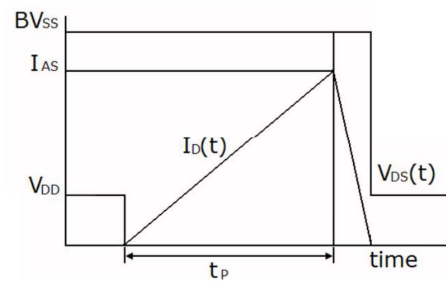
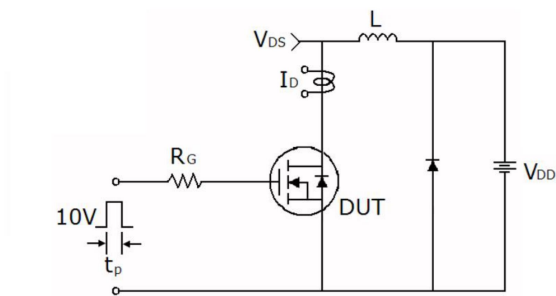
### (1) Gate charge test circuit & Waveform



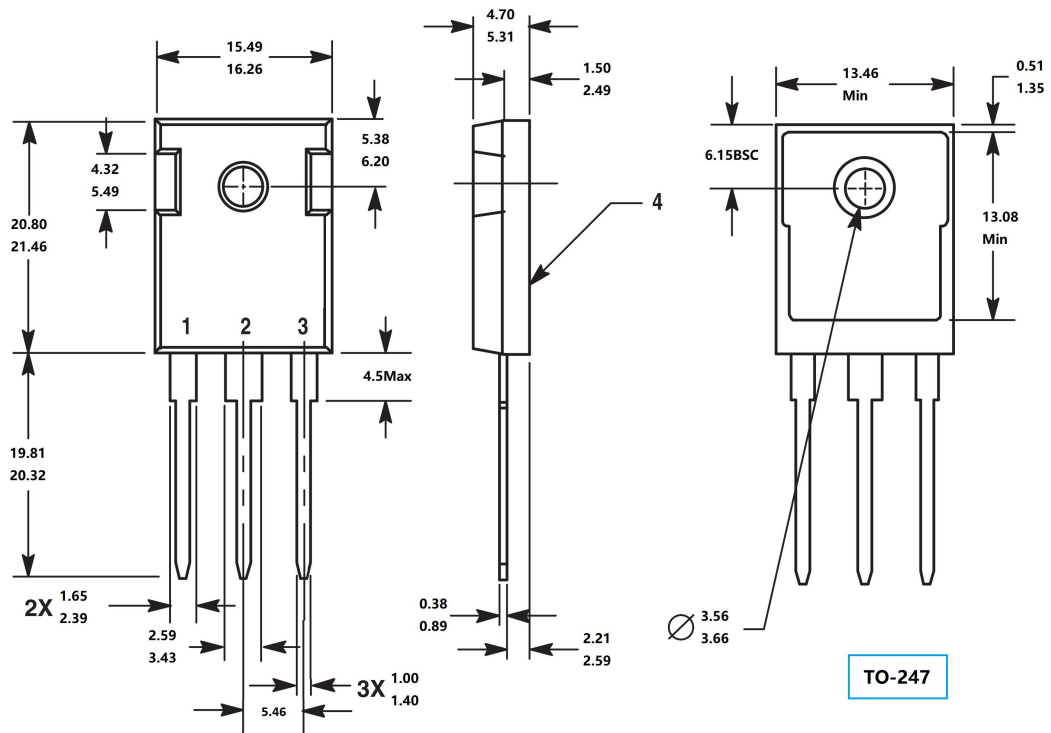
## (2) Switch Time Test Circuit



## (3) Unclamped Inductive Switching Test Circuit & Waveforms



## Package Mechanical DATA



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